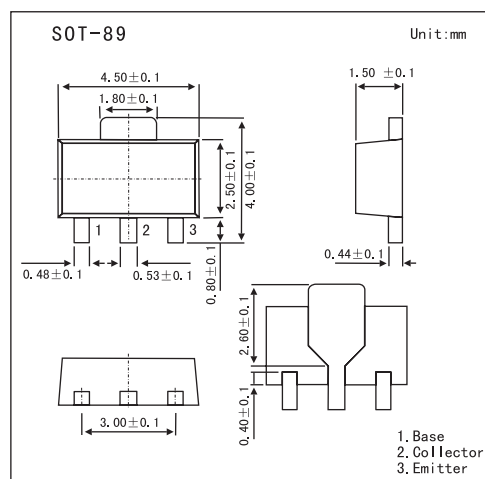


Medium Power Transistor

2SD2391

■ Features

- Low saturation voltage.
- Collector-emitter voltage =60V.
- PC=2 W (on 40×40×0.7mm ceramic board).

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	60	V
Collector-emitter voltage	V_{CE0}	60	V
Emitter-base voltage	V_{EB0}	6	V
Collector current	I_C	2	A
Collector power dissipation	P_C	0.5	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CB0}	$I_C=50\mu\text{A}$	60			V
Collector-emitter breakdown voltage	BV_{CE0}	$I_C=1\text{mA}$	60			V
Emitter-base breakdown voltage	BV_{EB0}	$I_E=50\mu\text{A}$	6			V
Collector cutoff current	I_{CBO}	$V_{CB}=50\text{V}$			0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB}=5\text{V}$			0.1	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=1\text{A}, I_B=50\text{mA}$		0.13	0.35	V
DC current transfer ratio	h_{FE}	$V_{CE}=-2\text{V}, I_C=-0.5\text{A}$	120		270	
Output capacitance	f_T	$V_{CE}=2\text{V}, I_E=-0.5\text{A}, f=100\text{MHz}$		210		MHz
Transition frequency	C_{ob}	$V_{CB}=10\text{V}, I_E=0\text{A}, f=1\text{MHz}$		21		pF

■ Marking

Marking	DTQ
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